

Device Modeling Report

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REMARK : SAMPLE B



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DIODE MODEL

Pspice model Parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

BIPOLAR JUNCTION TRANSISTOR MODEL

Pspice model parameter	Model description
NR	Reverse Emission Coefficient
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
CJC	Zero-bias Collector-Base Junction Capacitance
TF	Forward Transit Time
TR	Reverse Transit Time

VOLTAGE CONTROLLED VOLTAGE SOURCE MODEL(VCVS)

E<Name><(+)Node><(−)Node>VALUE={Expression}

E<Name><(+)Node><(−)Node>TABLE={Expression}

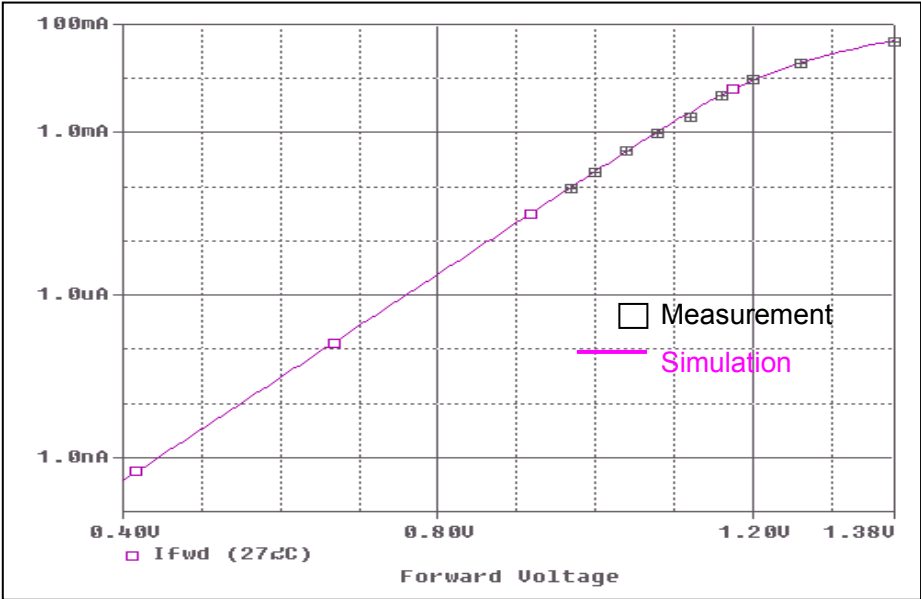
VOLTAGE CONTROLLED CURRENT SOURCE MODEL(VCCS)

E<Name><(+)Node><(–)Node>VALUE={Expression}

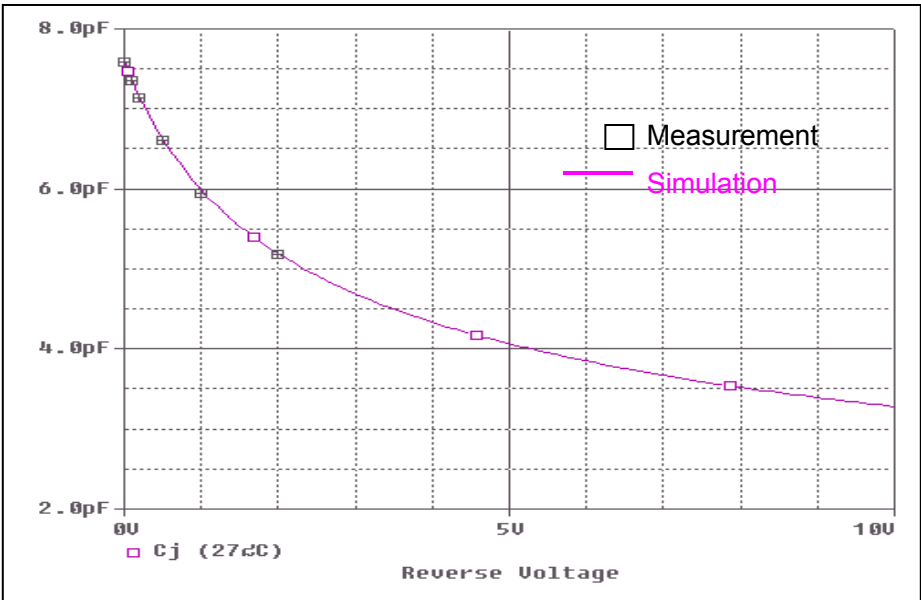
CURRENT CONTROLLED MODEL(W)

Pspice model parameter	Model description
IOFF	Controlling current to Off state
ION	Controlling current to On state
ROFF	Off Resistance
RON	On Resistance

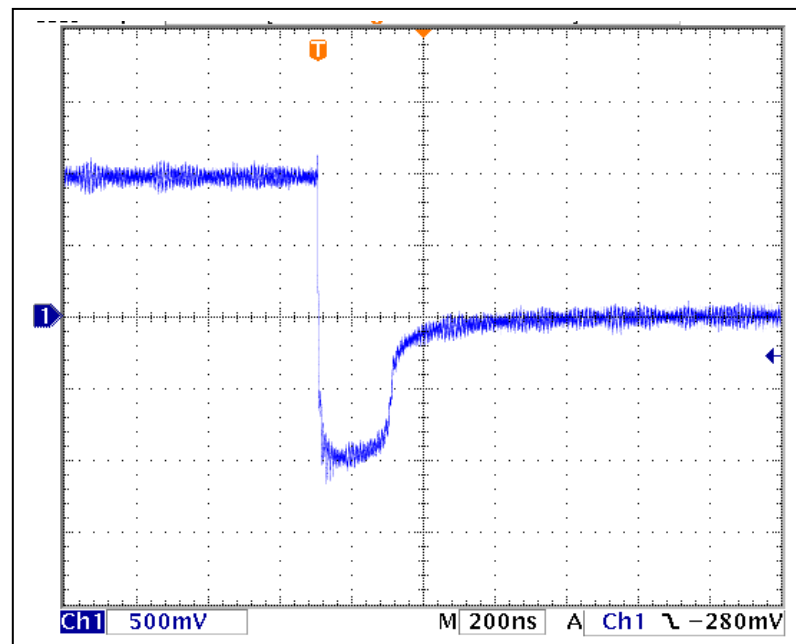
Input Device Forward Current Characteristics



Input Device Junction Capacitance Characteristics



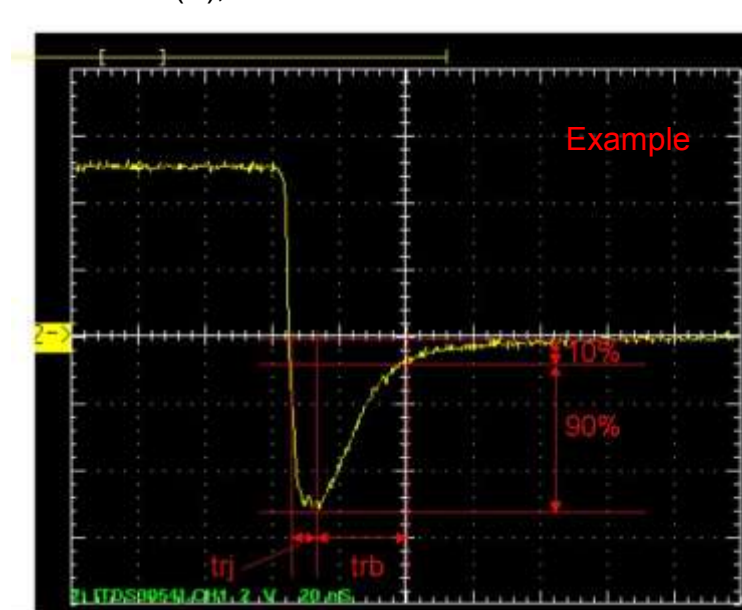
Input Device Reverse Recovery Characteristics



$t_{rj}=112\text{n(s)}$

$t_{rb}=180\text{n(s)}$

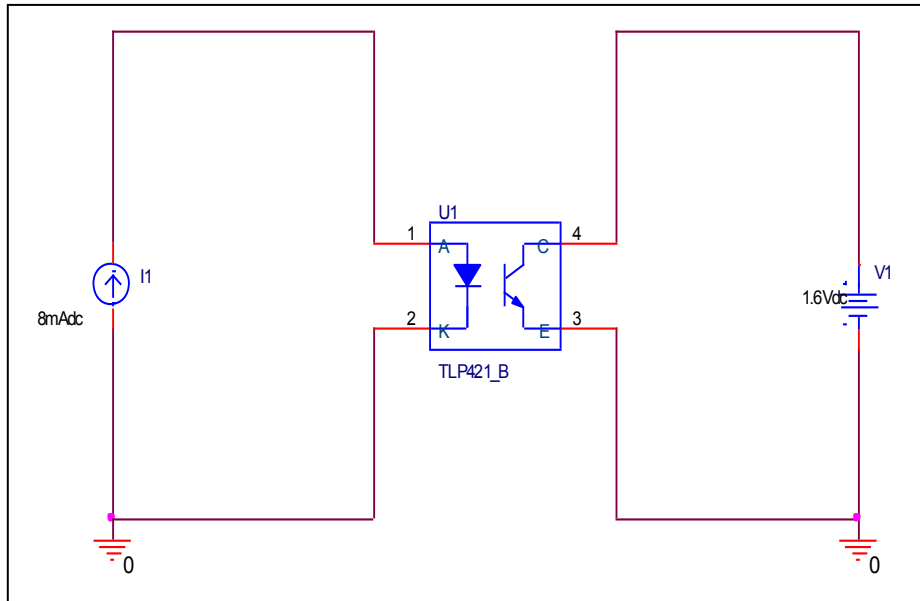
Conditions: $I_{fwd}=I_{rev}=0.04\text{(A)}$, $R_I=50$



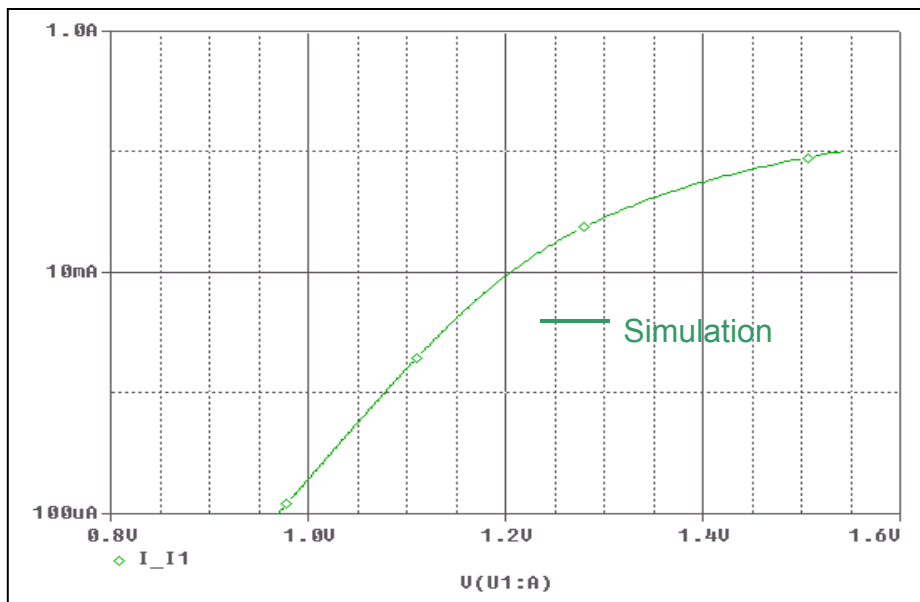
Relation between t_{rj} and t_{rb}

LED IV Curve Characteristics

Evaluation Circuit



Simulation result

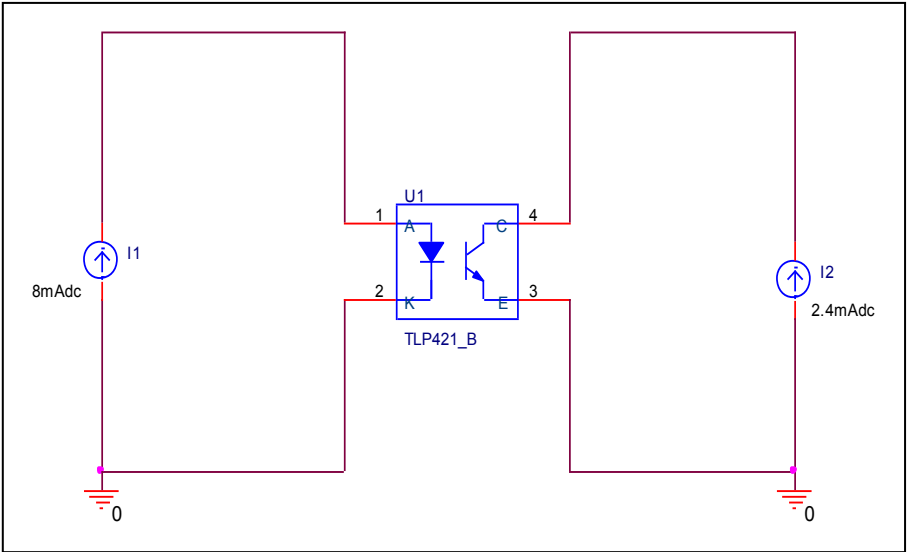


Comparison Table

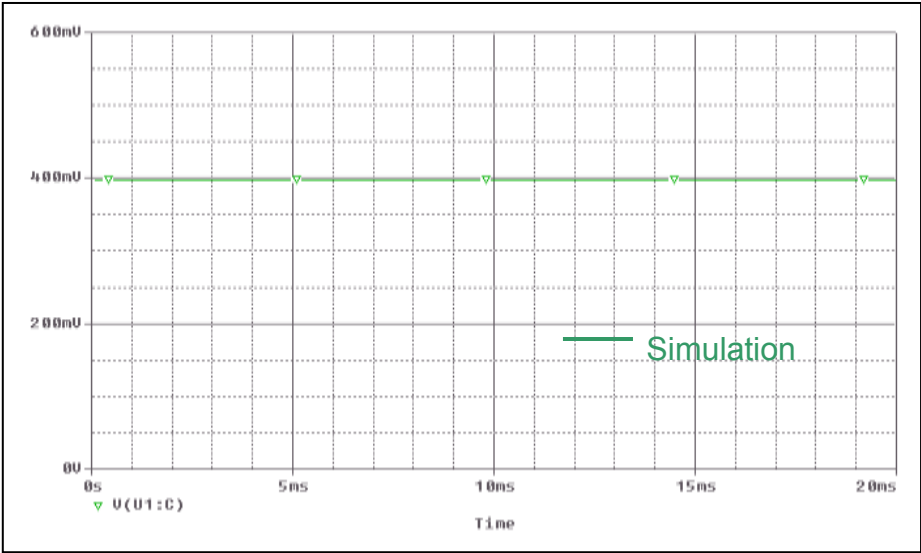
Ifwd(A)	Vfwd(V)		% Error
	Measurement	Simulation	
0.0001	0.97	0.969	-0.103
0.0002	1	1.0017	0.170
0.0005	1.04	1.0443	0.413
0.001	1.08	1.0771	-0.269
0.002	1.12	1.1113	-0.777
0.005	1.16	1.1606	0.052
0.01	1.2	1.2048	0.400
0.02	1.26	1.2615	0.119
0.05	1.38	1.3787	-0.094

Transistor Saturation Characteristics

Evaluation Circuit



Simulation result

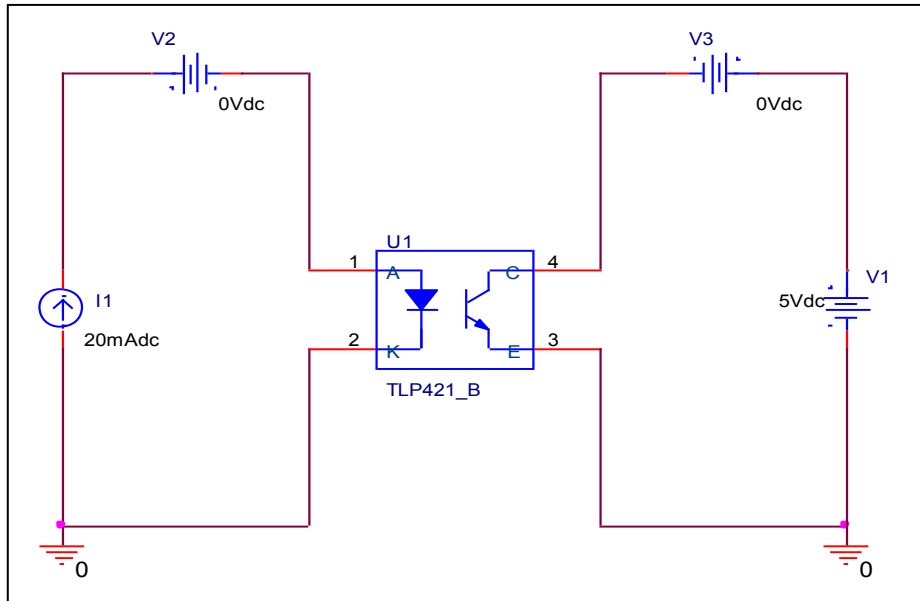


Comparison Table

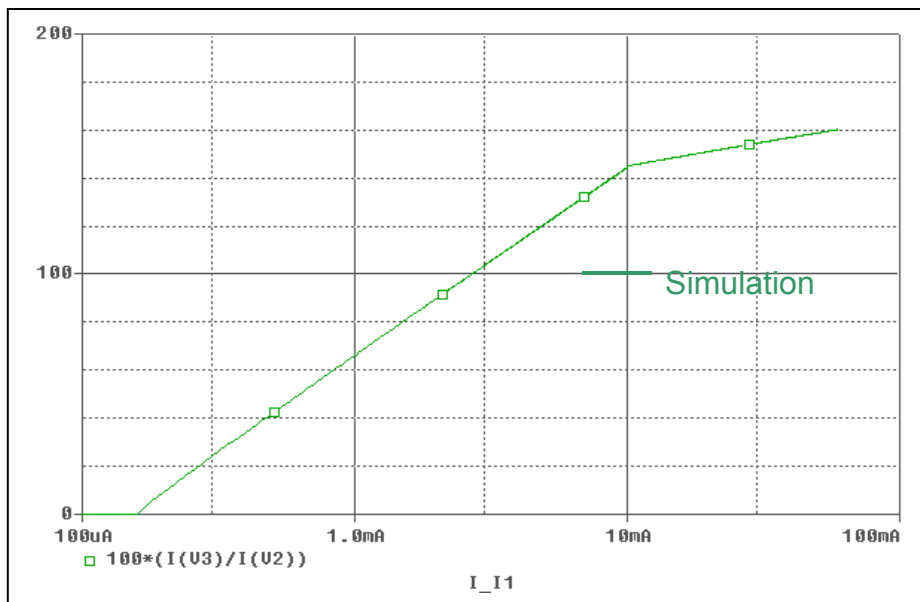
	Measurement	Simulation	% Error
Vce(sat) (V)	0.4	0.396	-1

CTR(Current Transfer Ratio) Characteristics

Evaluation Circuit



Simulation result



Rise Curve Table

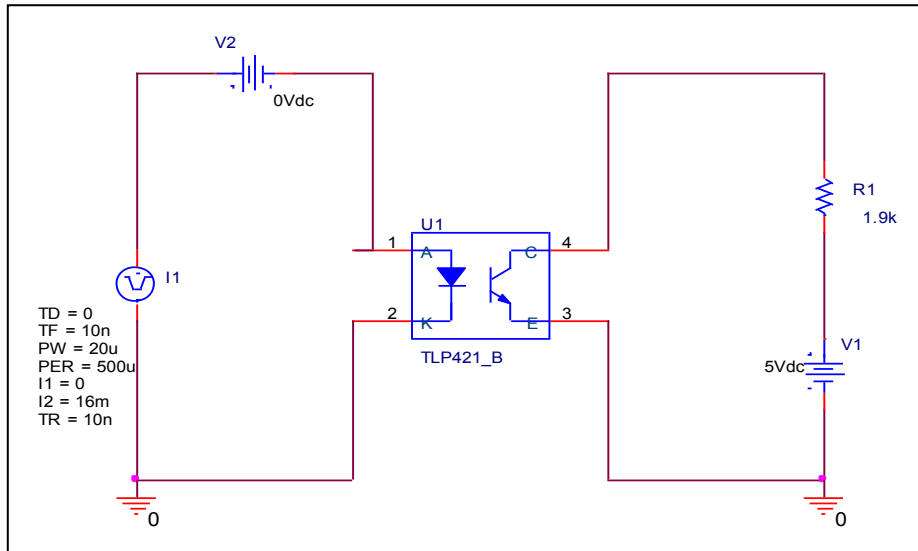
If(mA)	CTR(%)		% Error
	Measurement	Simulation	
0.5	42	42.249	0.593
1	65	66.258	1.935
2	93	89.961	-3.268
3	105	103.737	-1.203
4	115	113.482	-1.320
5	120	121.026	0.855
6	125	127.180	1.744
7	130	132.377	1.828
8	135	136.874	1.388
9	140	140.837	0.598
10	145	145.032	0.022

Fall Curve Table

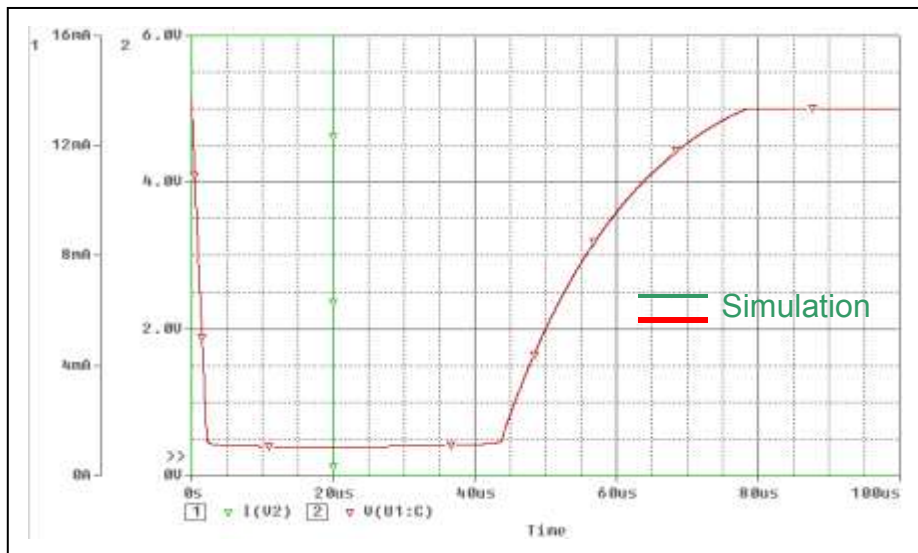
If(mA)	CTR(%)		% Error
	Measurement	Simulation	
10	145.00	145.032	0.022
20	149.00	151.081	1.397
30	155.00	154.552	-0.289
40	157.00	156.97	-0.019
50	159.00	158.811	-0.119
60	160.00	160.287	0.179

Switching Time Characteristics

Evaluation Circuit



Simulation result



Comparison Table

Vcc=5V, IC=16mA, RL=1.9kΩ	Measurement	Simulation	% Error
Ts (us)	25	25.091	0.364
Toff (us)	50	50.408	0.816